

2SC1030

Silicon NPN Transistors

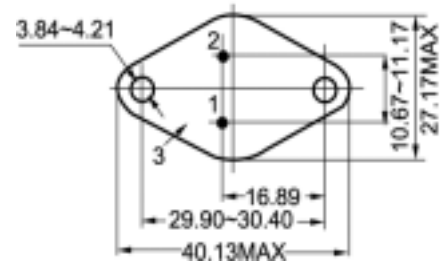
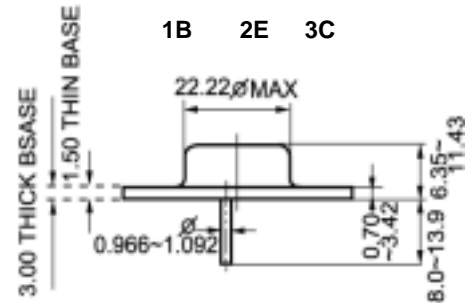


◆ Features

- With TO-3 package
- Low frequency power amplifications

◆ Absolute Maximum Ratings Tc=25°C

SYMBOL	PARAMETER	RATING	UNIT
V _{CBO}	Collector to base voltage	150	V
V _{CEO}	Collector to emitter voltage	80	V
V _{EBO}	Emitter to base voltage	6	V
I _C	Collector current-Continuous	6	A
P _D	Total Power Dissipation@TC=25°C	50	W
T _j	Junction temperature	200	°C
T _{stg}	Storage temperature	-55~200	°C



TO-3

◆ Electrical Characteristics Tc=25°C

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
V _{CEO}	Collector-Emitter Sustaining Voltage	I _C =0.2A; I _B =0	80			V
V _{CER}	Collector-Emitter Sustaining Voltage					
I _{CEO}	Collector Cutoff Current	V _{CE} =30V; I _B =0			2.0	mA
I _{EBO}	Emitter Cutoff Current	V _{EB} =6V; I _C =0			1.0	mA
I _{CBO}	Collector Cutoff Current	V _{CB} =30V; I _E =0			1.0	mA
V _{EBO}	Base-emitter breakdown voltage					
V _{CE(sat-1)}	Collector-emitter saturation voltages	I _C =5.0A; I _B =1.0A			1.5	V
V _{CE(sat-2)}	Collector-emitter saturation voltages					
V _{CE(sat-3)}	Collector-emitter saturation voltages					
h _{FE-1}	Forward current transfer ratio	I _C =1A; V _{CE} =5V	35		200	
h _{FE-2}	Forward current transfer ratio	I _C =5A; V _{CE} =5V	22			
h _{FE-3}	Forward current transfer ratio					
V _{BE(on)}	Base-emitter On voltages					
f _T	Current Gain-Bandwidth Product	I _C =1A; V _{CE} =5V		10		MHz
h _{fe}	Small-Signal Current Gain					